

Hong Jin Kim

List of Publications by Year in descending order

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Version: 2024-02-01

17
papers

206
citations

1163117

8
h-index

1125743

13
g-index

18
all docs

18
docs citations

18
times ranked

148
citing authors

#	ARTICLE	IF	CITATIONS
1	Study of the cross contamination effect on post CMP in situ cleaning process. Microelectronic Engineering, 2015, 136, 36-41.	2.4	46
2	MD Simulations of Microstructure Evolution during High-Velocity Sliding between Crystalline Materials. Tribology Letters, 2007, 28, 299-306.	2.6	40
3	First observation on the feasibility of scratch formation by padâ€‘particle mixture in CMP process. Applied Surface Science, 2012, 258, 8298-8306.	6.1	28
4	Effect of pad surface roughness on material removal rate in chemical mechanical polishing using ultrafine colloidal ceria slurry. Electronic Materials Letters, 2013, 9, 155-159.	2.2	15
5	Effect of Brush Treatment and Brush Contact Sequence on Cross Contaminated Defects during CMP in-situ Cleaning. Journal of the Korean Society of Tribologists and Lubrication Engineers, 2015, 31, 239-244.	0.1	11
6	Effect of Controlling Abrasive Size in Slurry for Tungsten Contact CMP Process. ECS Journal of Solid State Science and Technology, 2019, 8, P3206-P3211.	1.8	10
7	Effects of Pad Temperature on the Chemical Mechanical Polishing of Tungsten. ECS Journal of Solid State Science and Technology, 2014, 3, P310-P314.	1.8	9
8	Study on the Mechanism of Nano-Flake Defect during Tungsten Contact Chemical Mechanical Polishing. ECS Journal of Solid State Science and Technology, 2018, 7, P175-P179.	1.8	9
9	A New Approach to the Formation Mechanism of Tungsten Void Defect in Chemical Mechanical Polishing. ECS Journal of Solid State Science and Technology, 2018, 7, P693-P697.	1.8	9
10	Effect of post CMP in-situ cleaning and its optimization on the defect improvement: CFM: Contamination free manufacturing. , 2016, , .		7
11	Metal Flake Defect and Its Formation Mechanism during Replacement Metal Gate CMP Process. ECS Journal of Solid State Science and Technology, 2016, 5, P637-P640.	1.8	6
12	Abrasive for Chemical Mechanical Polishing. , 2018, , .		5
13	Effect of Reactive Ion Etch on the Polishing Selectivity during Silicon Nitride Chemical Mechanical Polishing for Sub-10 nm Logic Device. ECS Journal of Solid State Science and Technology, 2017, 6, P101-P104.	1.8	4
14	Brush cleaning effect on tungsten voids defect in chemical mechanical polishing: CFM: Contamination free manufacturing. , 2018, , .		2
15	Storage Temperature Effects on the Slurry Health Parameters and SiO ₂ Removal Rates during Chemical Mechanical Polishing. ECS Journal of Solid State Science and Technology, 2021, 10, 104002.	1.8	1
16	Effect of brush cleaning on defect generation in post copper CMP. Microelectronic Engineering, 2022, 261, 111808.	2.4	1
17	MICROSTRUCTURES PRODUCED BY DYNAMIC FRICTION. , 2008, , .		0